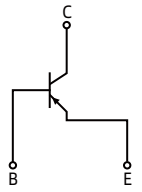
TL-BC857CW

SOT-323 Plastic-Encapsulate Transistors (PNP)

Features

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

SOT-323



Equivalent Circuit

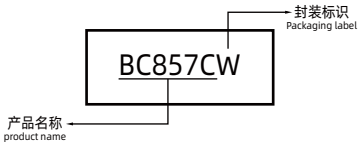
Absolute Maximum Ratings(T_A=25℃)

Symbol	Parameter	Value	Uniat
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.1	A
P_C	Collector Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	833	℃/W
T_J,T_{stg}	Operation Junction And Storage Temperature Range	-55～+150	℃

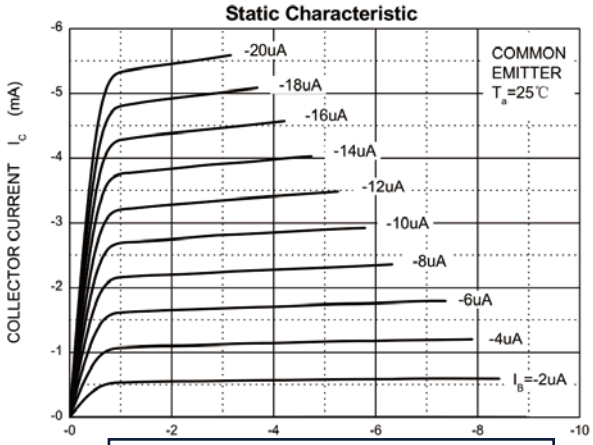
Electrical Characteristics (T_A=25℃ unless otherwise specified)

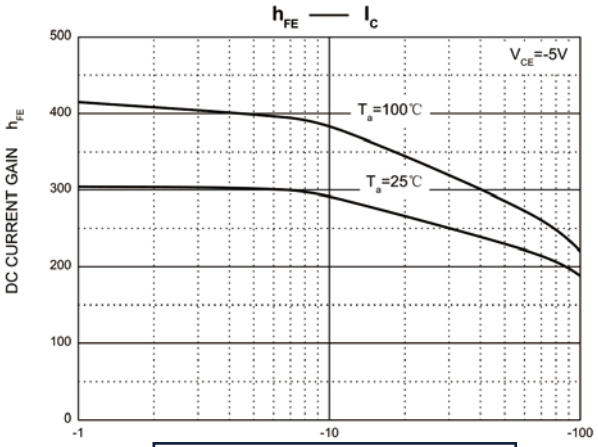
Symbol	Parameter	Test conditions	Min	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-10μA, I_E=0	-50		V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA, I_B=0	-45		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1μA, I_C=0	-5		V
I_{CBO}	Collector cut-off current	V_{CB}= -30V , I_E=0		-15	nA
h_{FE}	DC current gain	V_{CE}=-5V,I_C= -2mA	420	800	
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=-100mA, I_B=-5mA		-0.65	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C=-100mA, I_B=-5mA		-1.1	V
f_T	Transition frequency	V_{CE}=-5V,I_C=-10mA,f=100MHz	100		MHz
C_{ob}	Collector output capacitance	V_{CB}=-10V,f=1MHz		4.5	pF

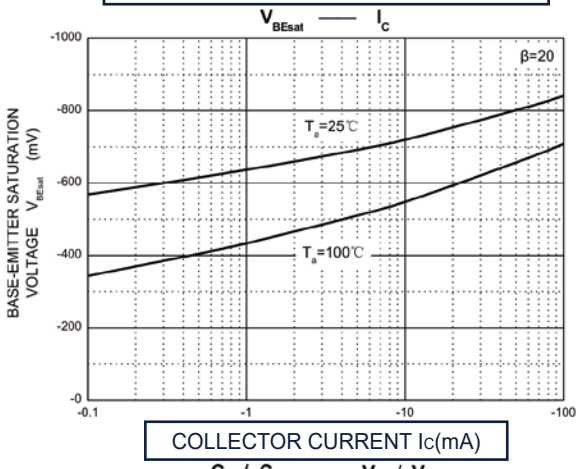
Ordering information

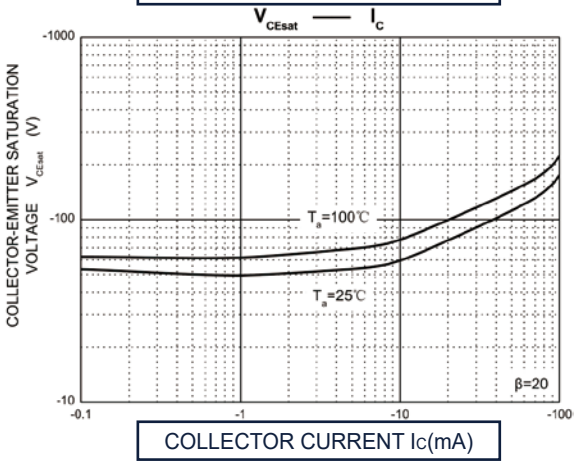
Product ID	Pack	Naming rule	Marking	hFE(1)	Qty(PCS)
BC857CW	SOT-323		3G	420-800	3000

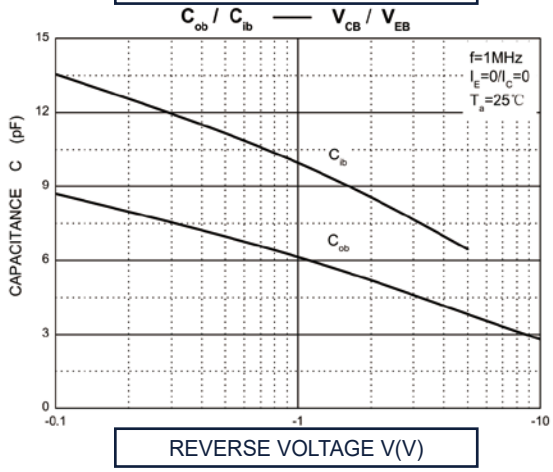
Typical Characteristics

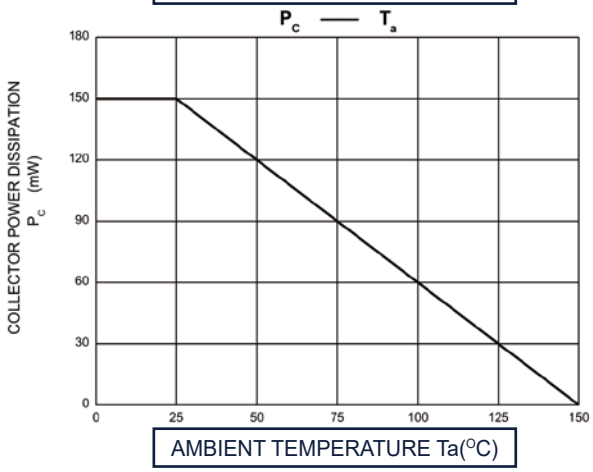




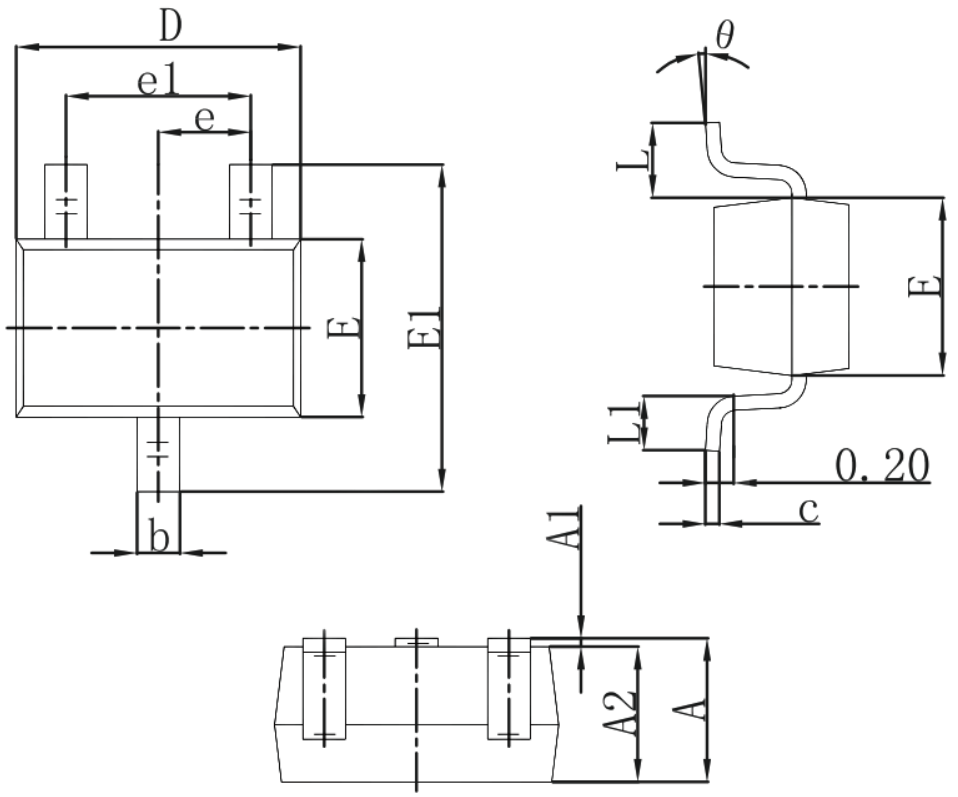








SOT-323 Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	1.350	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°